Unit: mm

TOSHIBA Diode Silicon Epitaxial Schottky Barrier Type

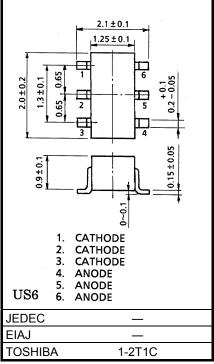
# HN2S03FU

#### **High Speed Switching Application**

HN2S03FU is composed of 3 independent diodes.
Low forward voltage : V<sub>F (3)</sub> = 0.50V (typ.)
Low reverse current : I<sub>R</sub>= 0.5µA (max)
Small total capacitance : C<sub>T</sub> = 3.9pF (typ.)

### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse Voltage	$V_{RM}$	25	V
Reverse voltage	V <sub>R</sub>	20	V
Maximum (peak) forward current	I <sub>FM</sub>	100 *	mA
Average forward current	IO	50 *	mA
Surge current (10ms)	I <sub>FSM</sub>	1 *	Α
Power dissipation	Р	200 **	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55~125	°C
Operating temperature range	T <sub>opr</sub>	<b>−</b> 40~110	°C



Weight: 6.2mg(Typ.)

Note: Using continuously under heavy loads (e.g. the application of high

temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Electrical Characteristics (Q1, Q2, Q3 Common, Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Forward voltage	V <sub>F (1)</sub>	_	I <sub>F</sub> = 1mA	ı	0.33	-		
	V <sub>F (2)</sub>	_	I <sub>F</sub> = 5mA	1	0.38	_	V	
	V <sub>F (3)</sub>	_	I <sub>F</sub> = 50mA	_	0.50	0.55		
Reverse current	I <sub>R</sub>	_	V <sub>R</sub> = 20V	_	_	0.5	μA	
Total capacitance	C <sub>T</sub>	_	$V_R = 0$ , $f = 1MH_Z$	-	3.9	-	pF	

<sup>\* :</sup> This is absolute maximum rating of single diode (Q1 or Q2 or Q3). In the case of using 2 or 3 diodes, the absolute maximum ratings per diodes is 75 % of the single diode one.

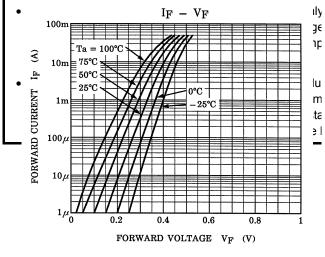
<sup>\*\* :</sup>Total rating

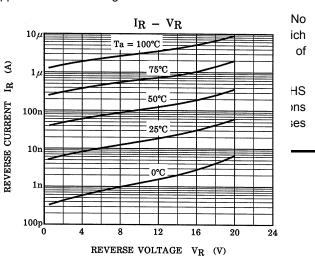
stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.

set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.

• The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, ment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither into ted for usage in equipment that requires extraordinarily high quality and/or reliability or a r re of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended omic energy control instruments, airplane or Α8 spaceship instruments, transportation instrumen struments, combustion control instruments, medical instruments, all types of safety devices Usage of TOSHIBA products listed in his ᆸ document shall be made at the customer's own ris

• The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.

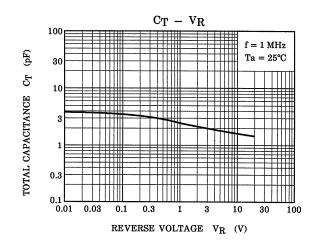


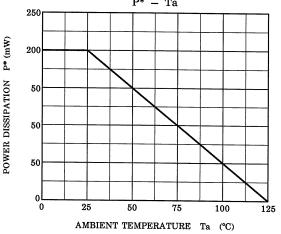


## Pin Assignment (Top View)

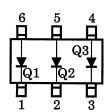
#### Marking

2





\* : Total Rating



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